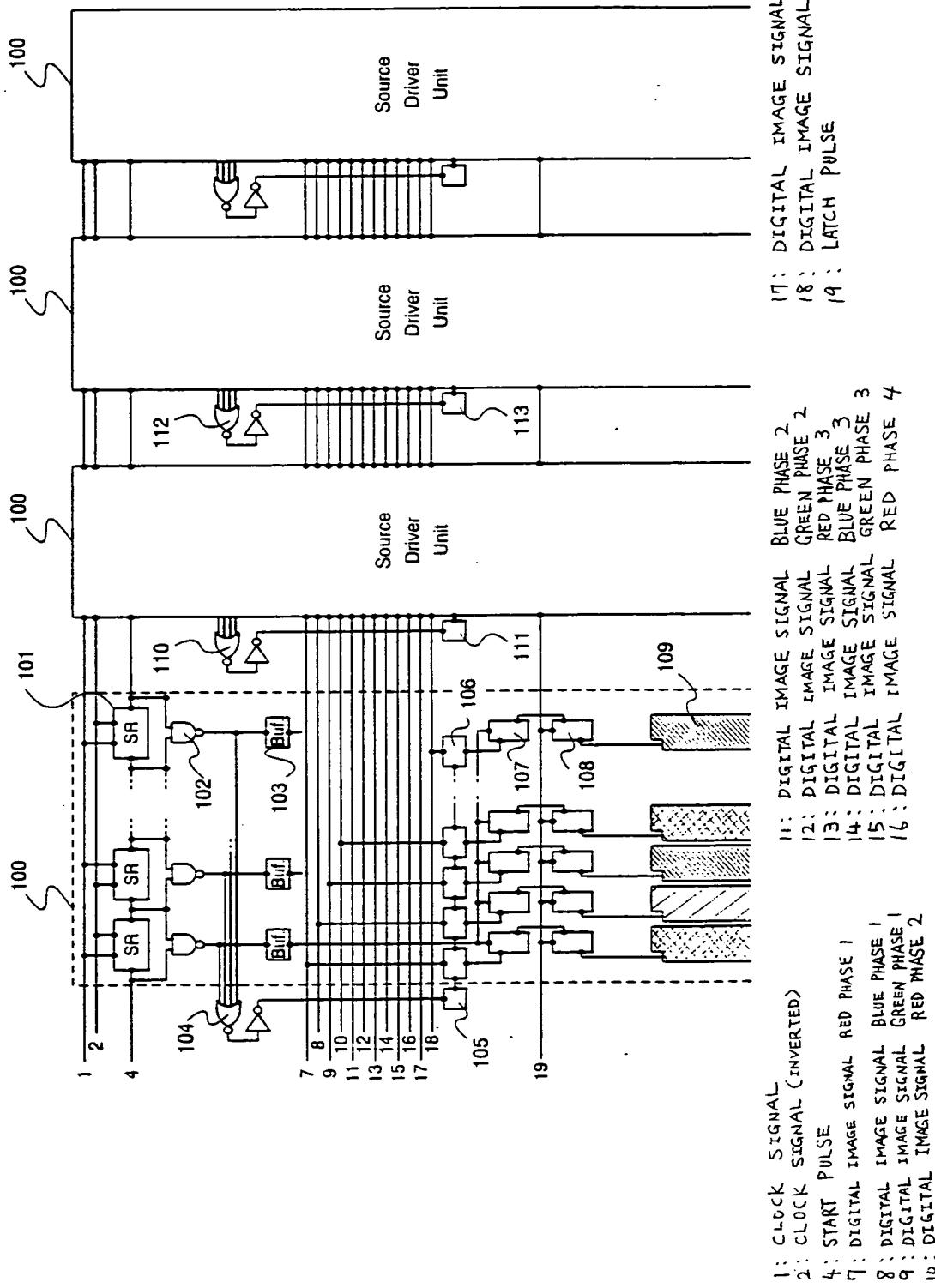


TM500T-6260Z660

Fig. 1



10500P-92602660

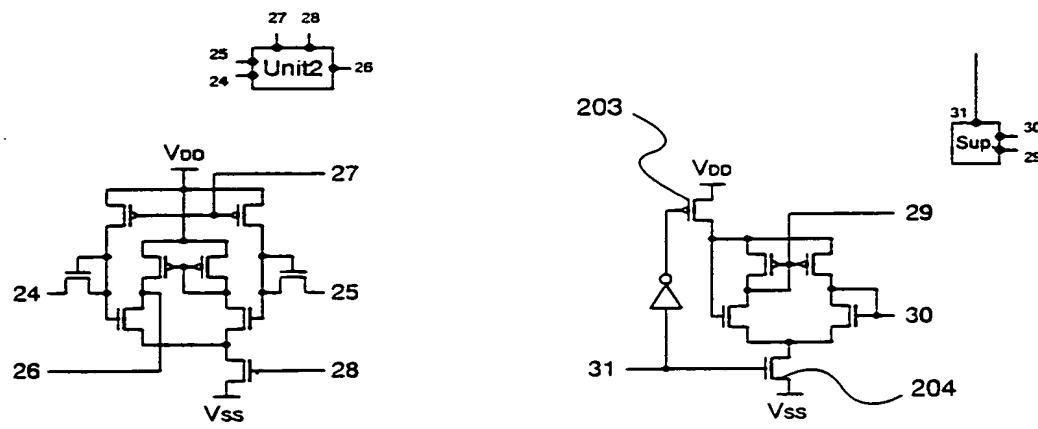
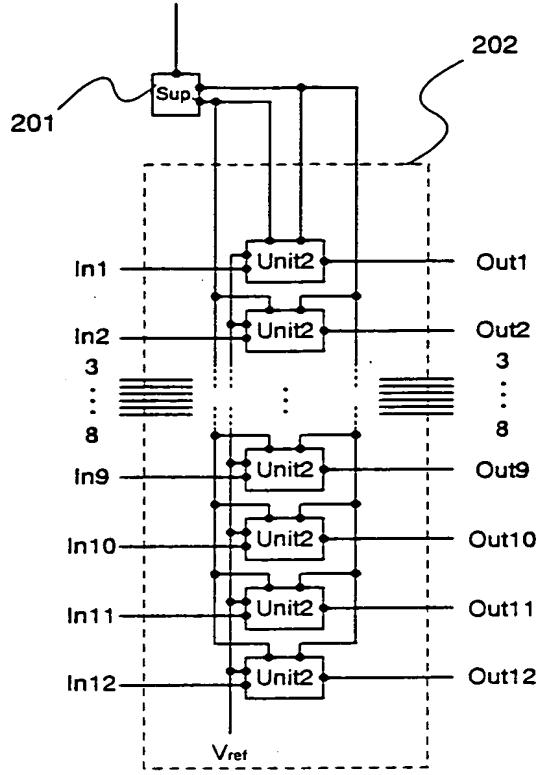


Fig. 2

"TOSOUD" 62602660

Fig. 3

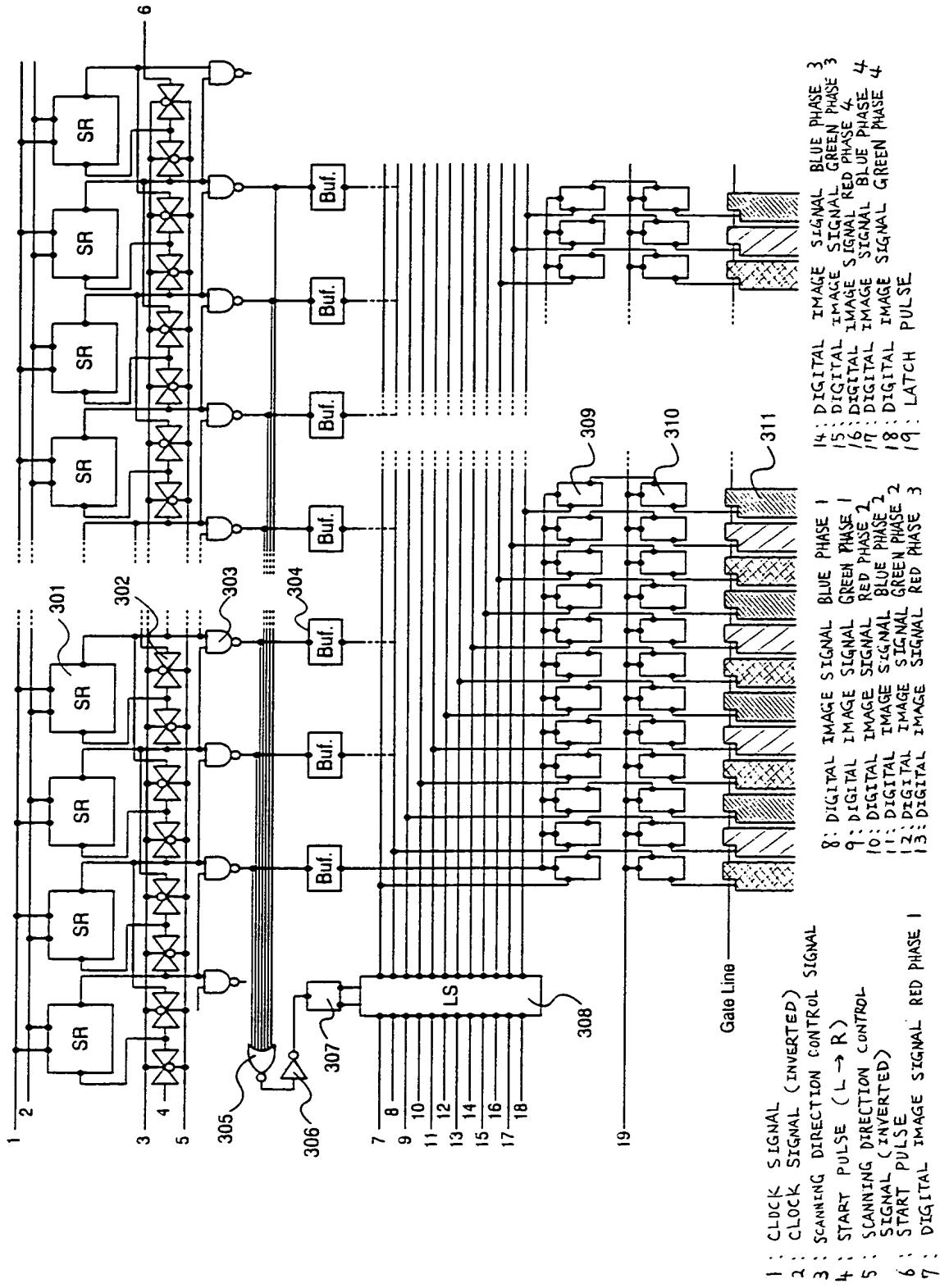
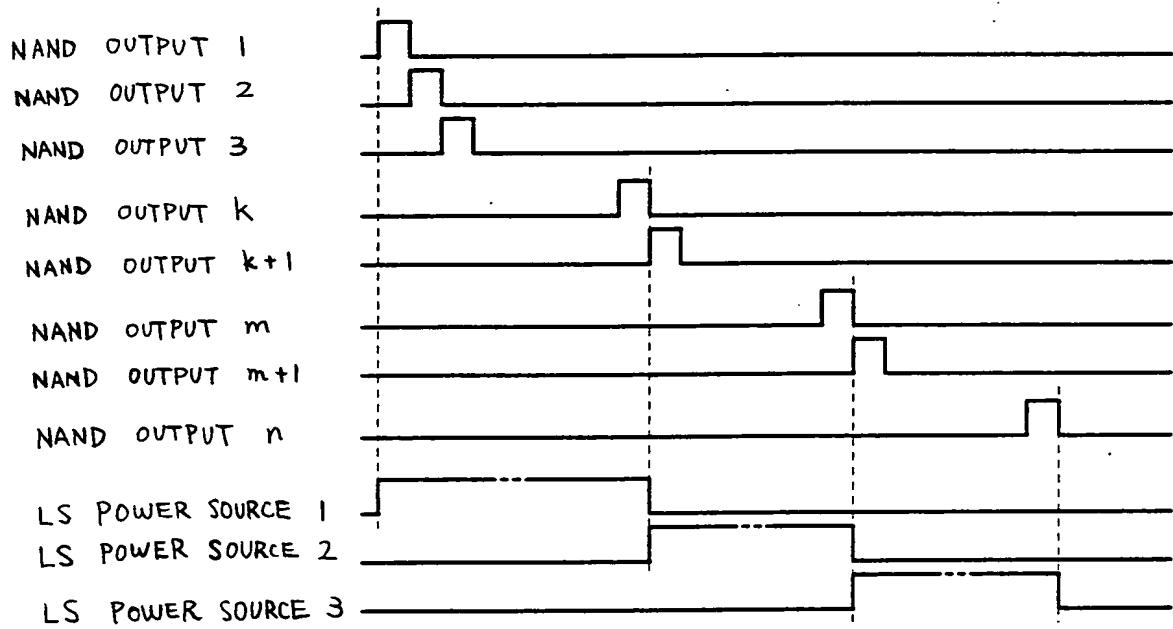


Fig. 4



"TOSHIBA" 62604660

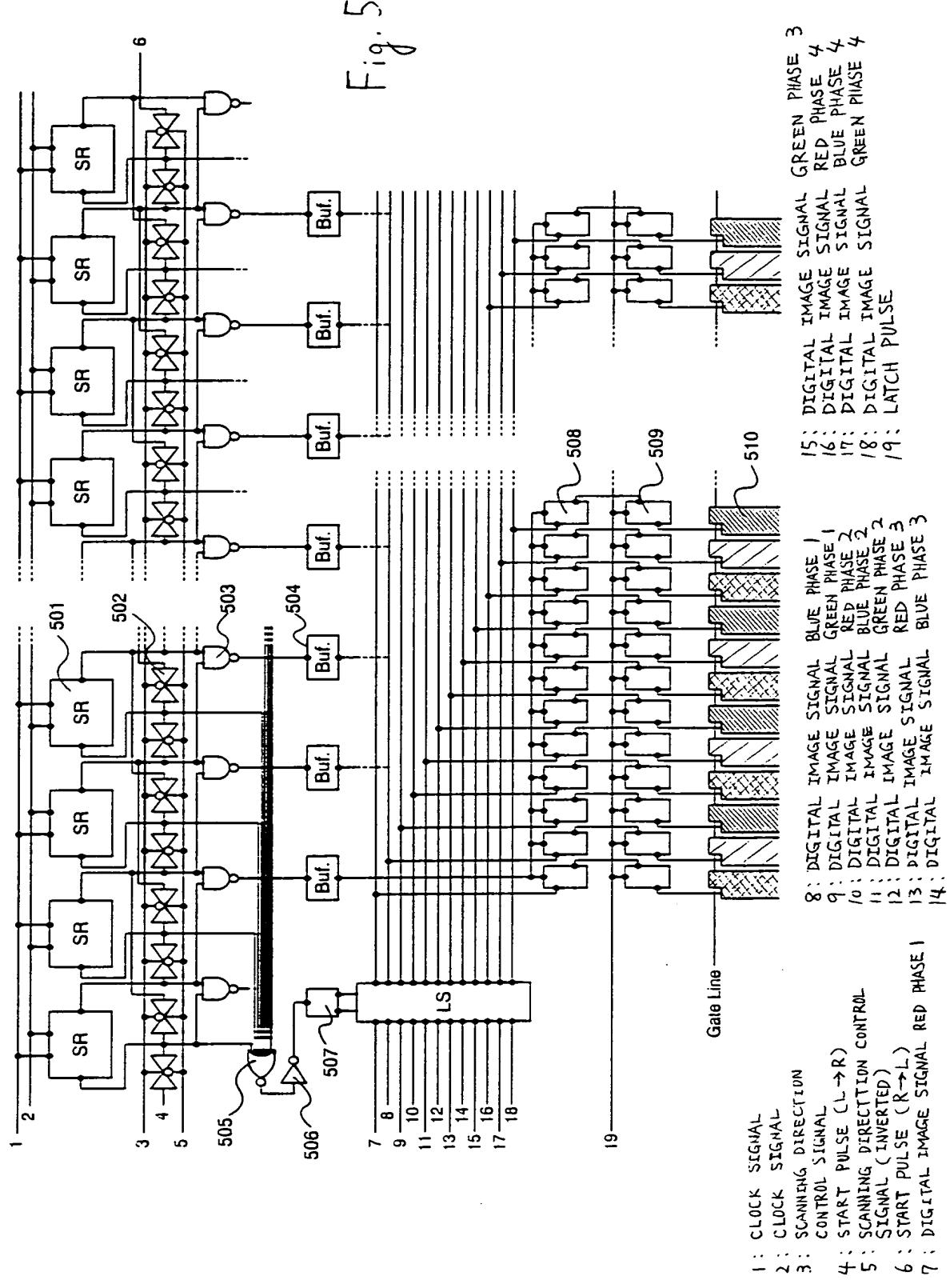
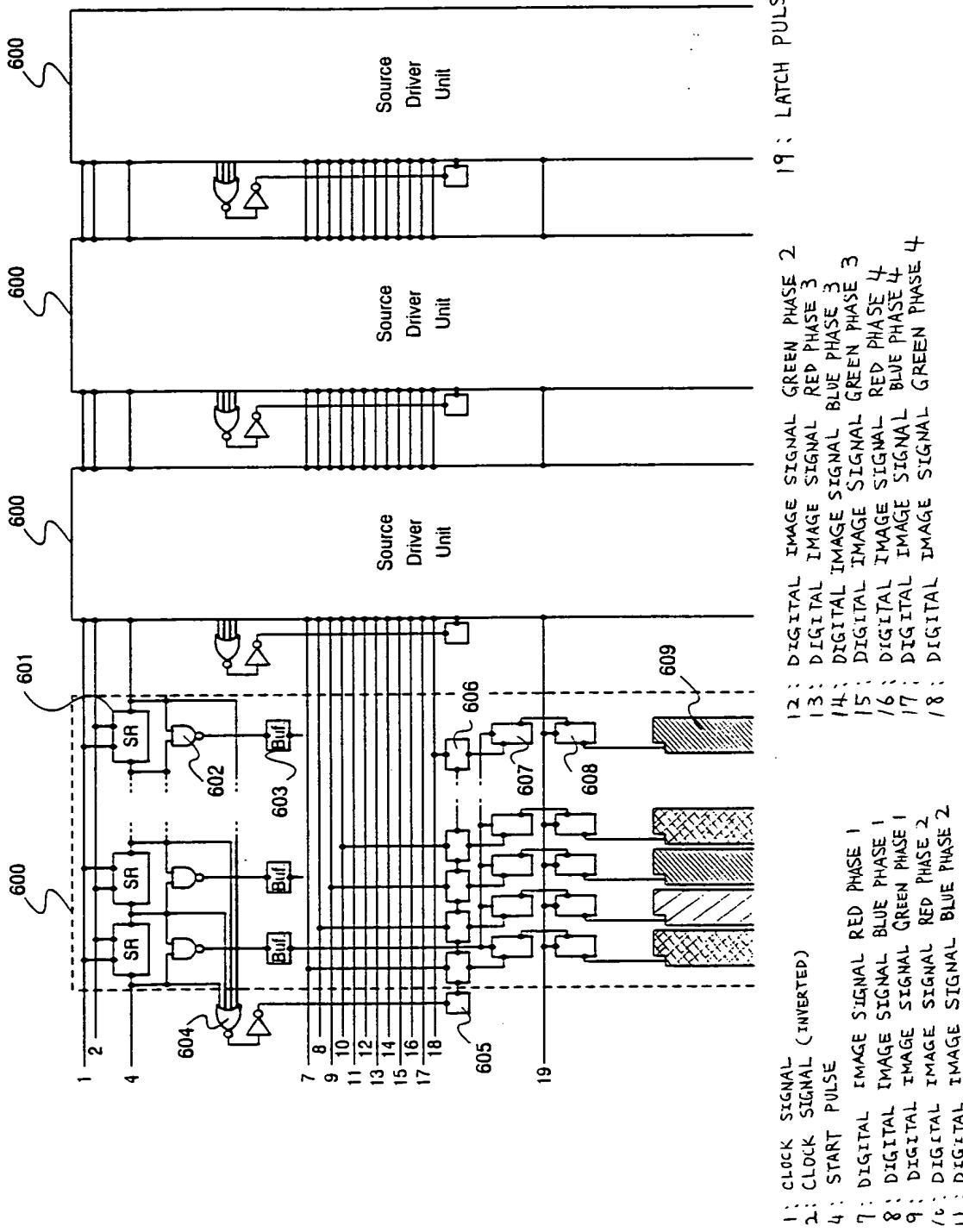
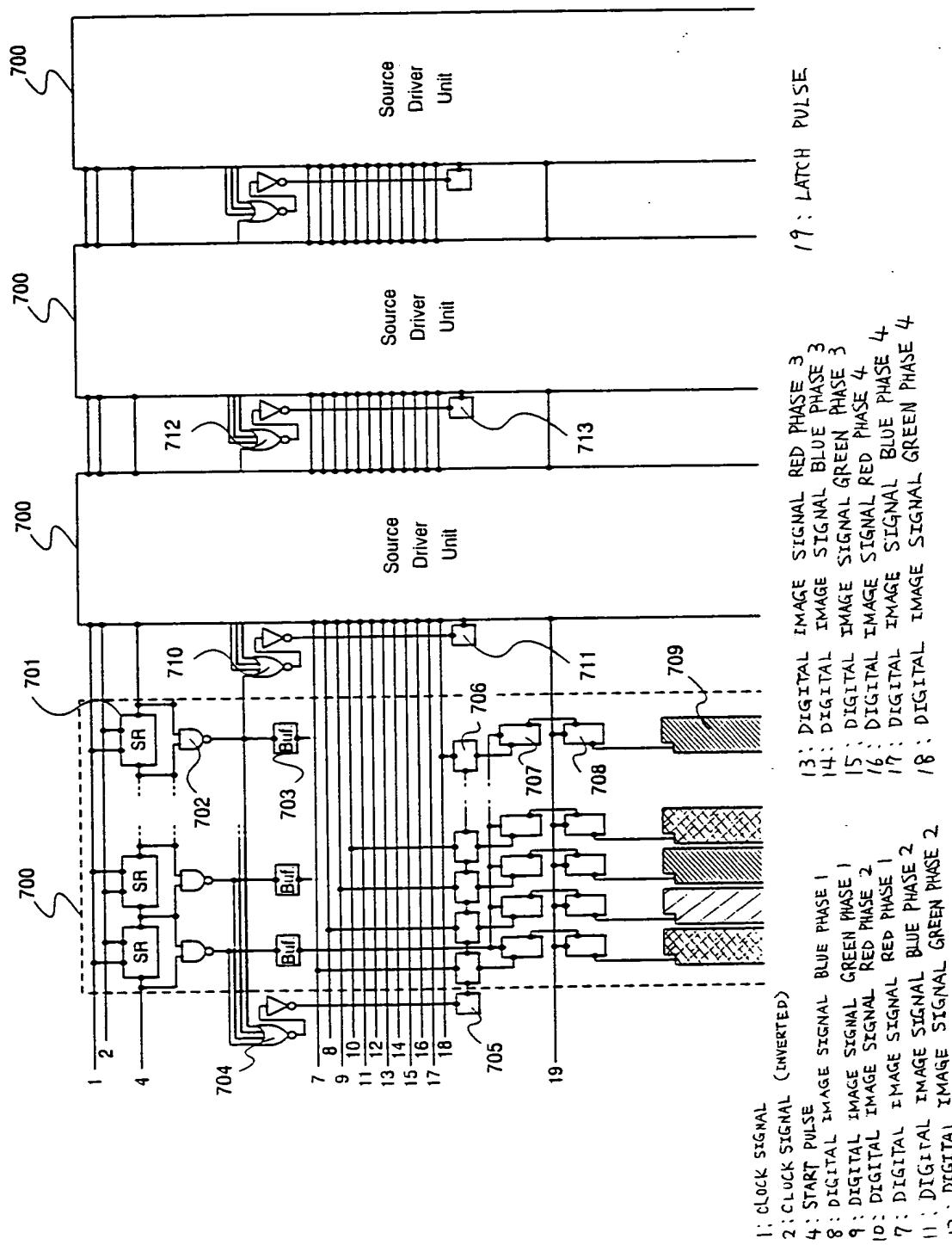


Fig. 6





TO500T-62697660

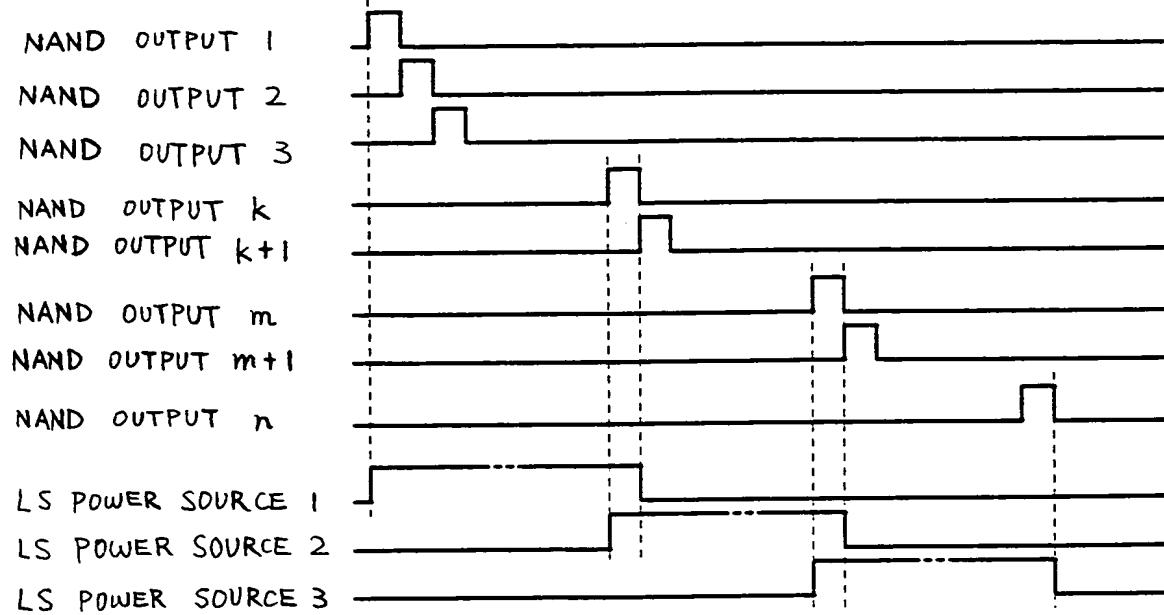
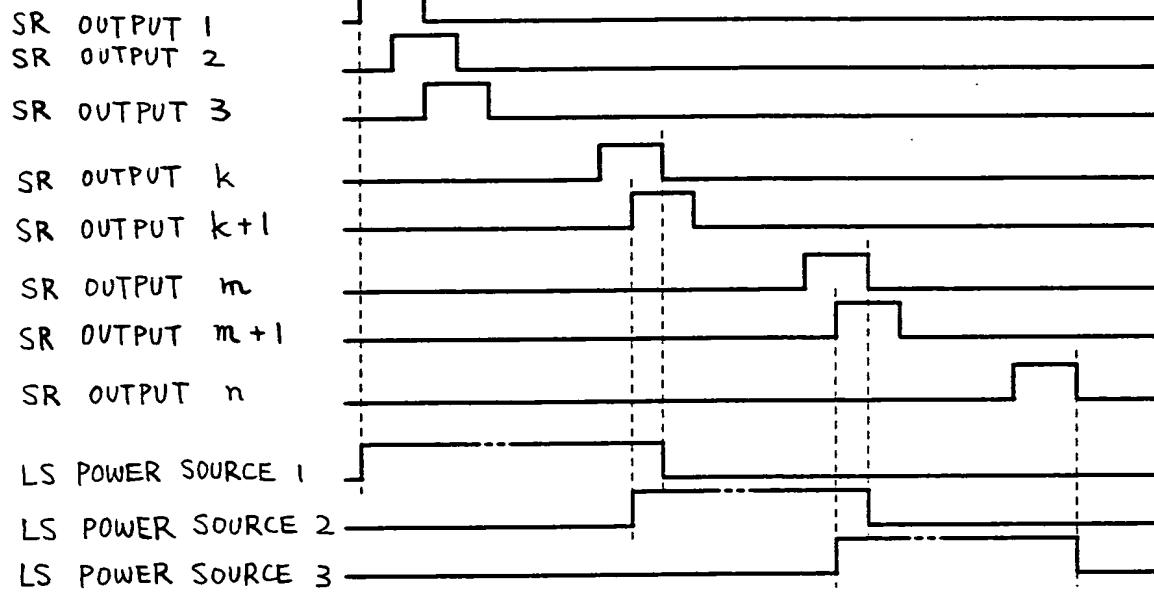
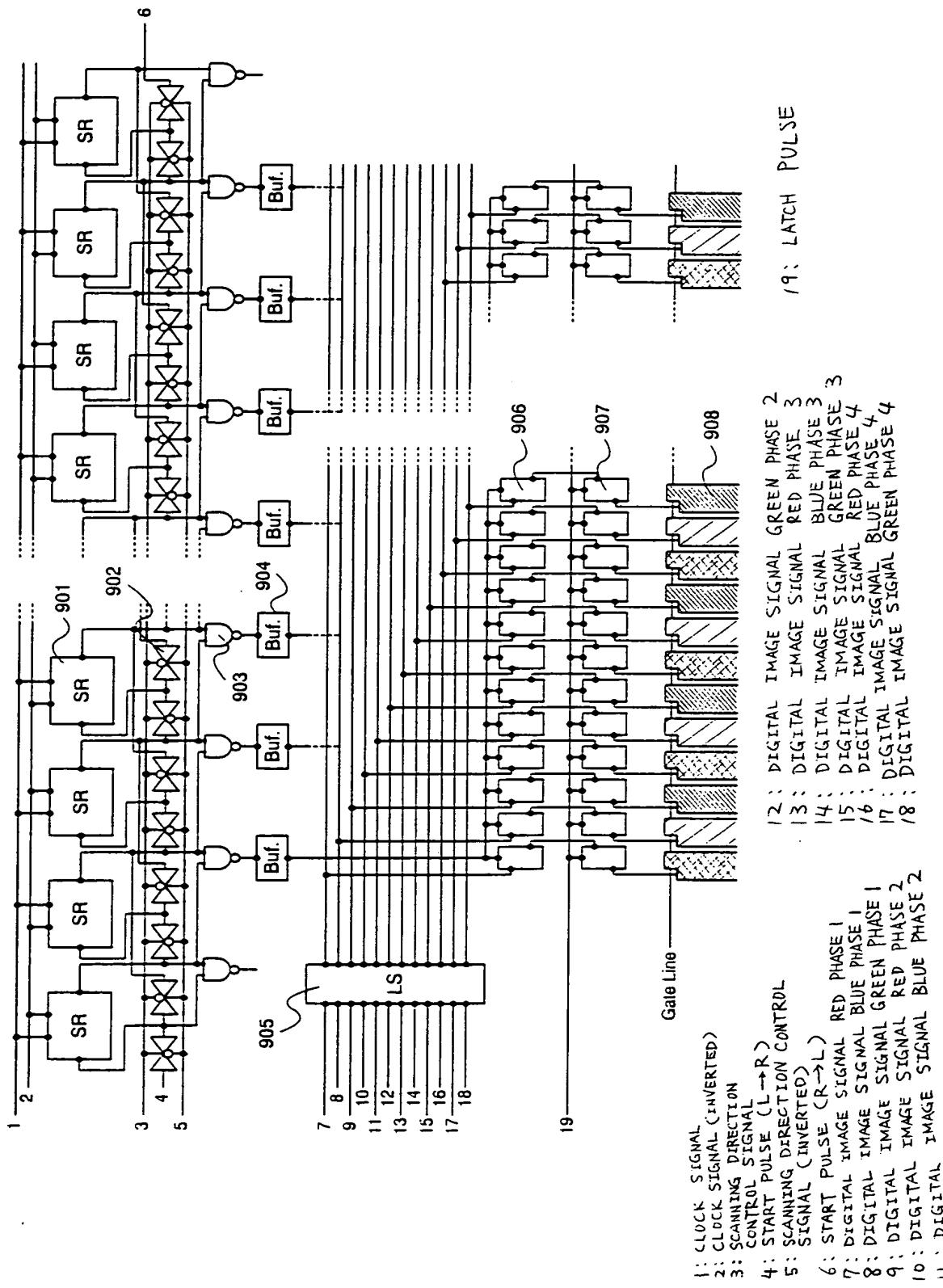


Fig. 9



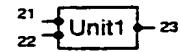
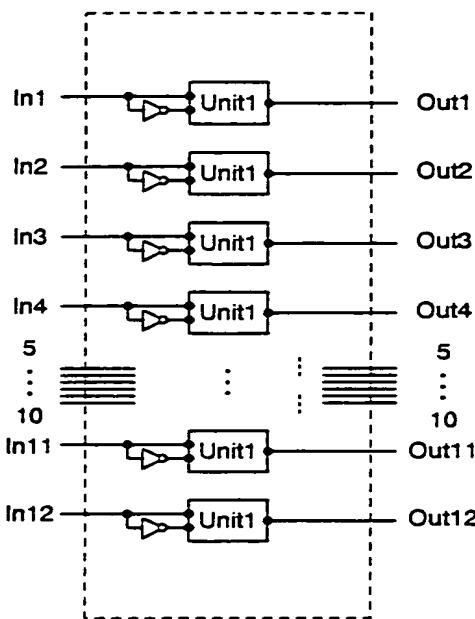


Fig. 10(A)

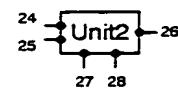
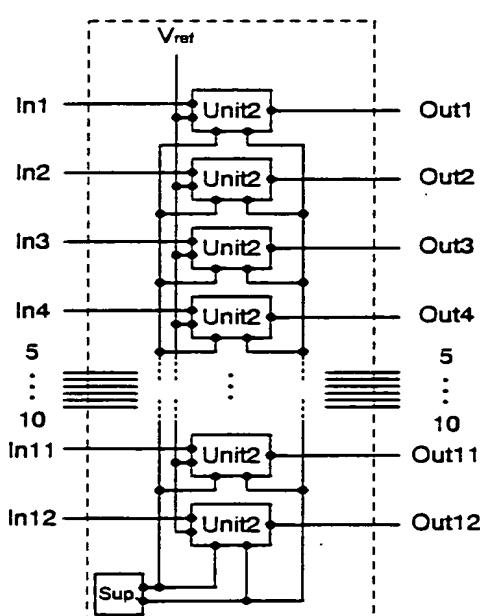
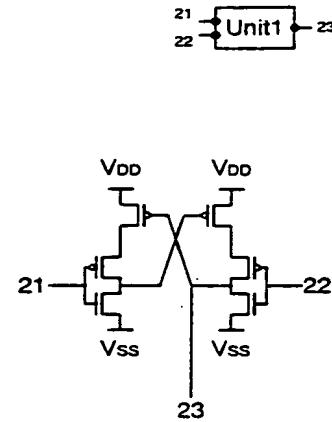
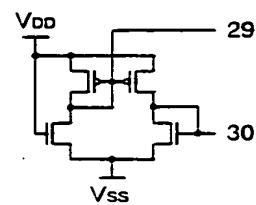
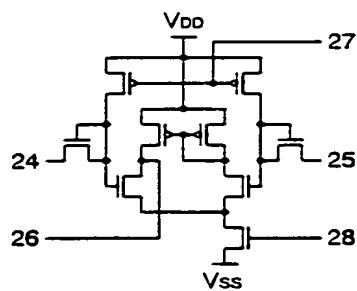


Fig. 10(B)



KO500T-62604660

FORMATION OF SEMICONDUCTOR ISLAND AND FIRST AND SECOND CONDUCTIVE FILMS FOR GATE ELECTRODE

Fig. II(A)

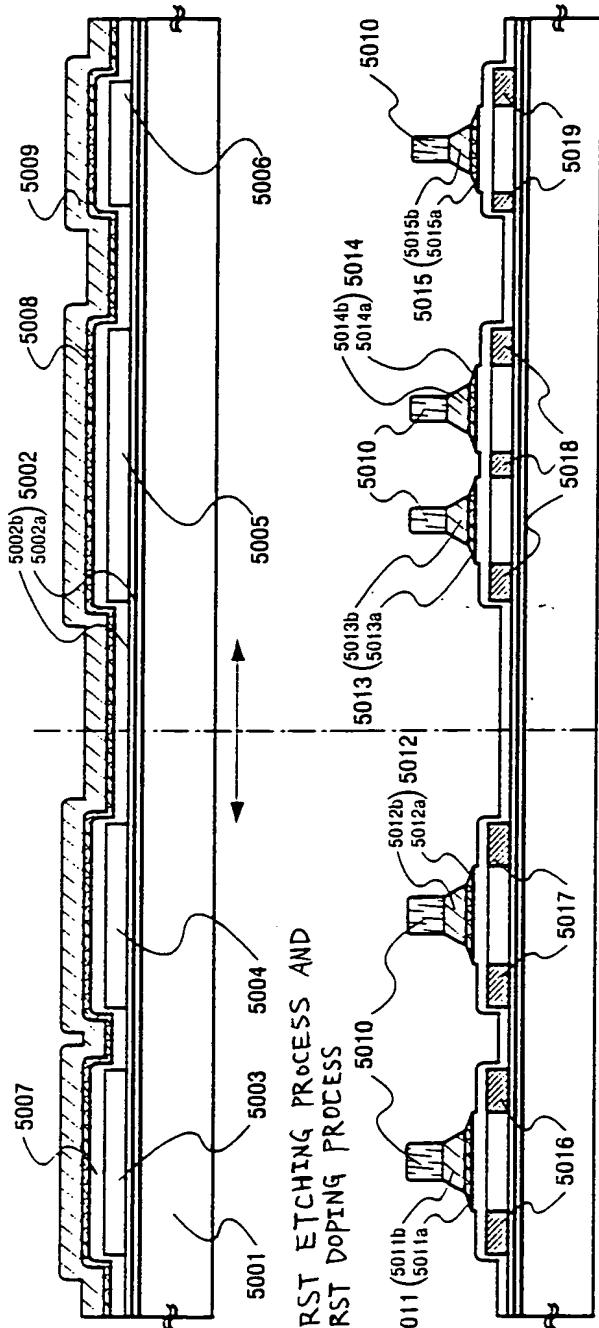


Fig. II(B)
FIRST ETCHING PROCESS AND
FIRST DOPING PROCESS 5010

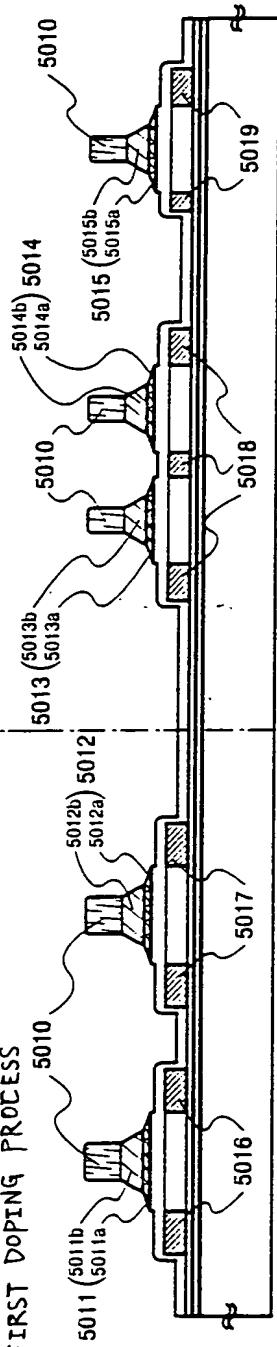
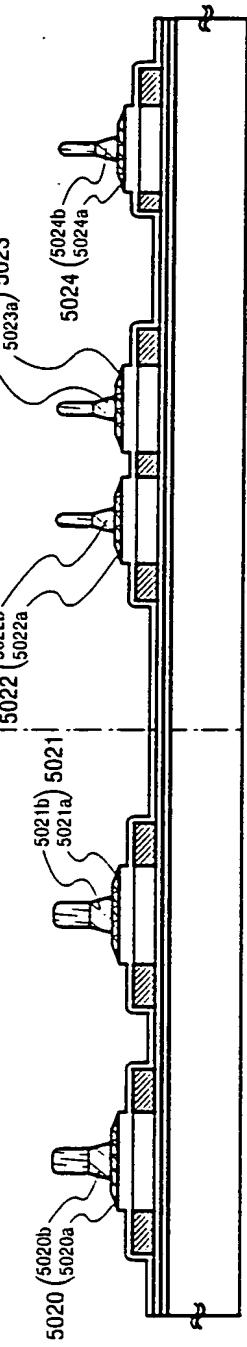


Fig. II(C)
SECOND ETCHING PROCESS



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Fig.12(A) SECOND DOPING PROCESS

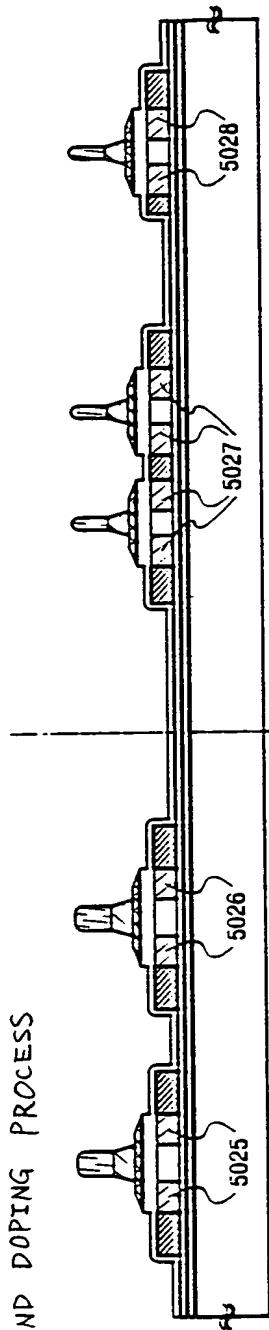


Fig.12(B)

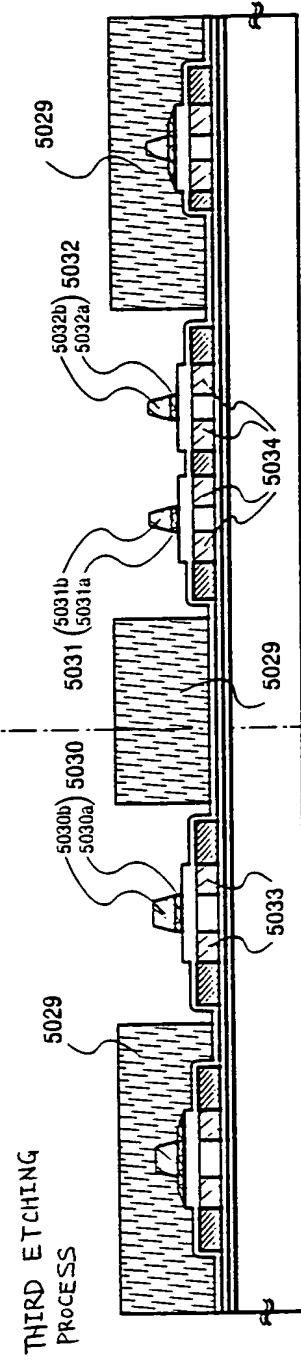
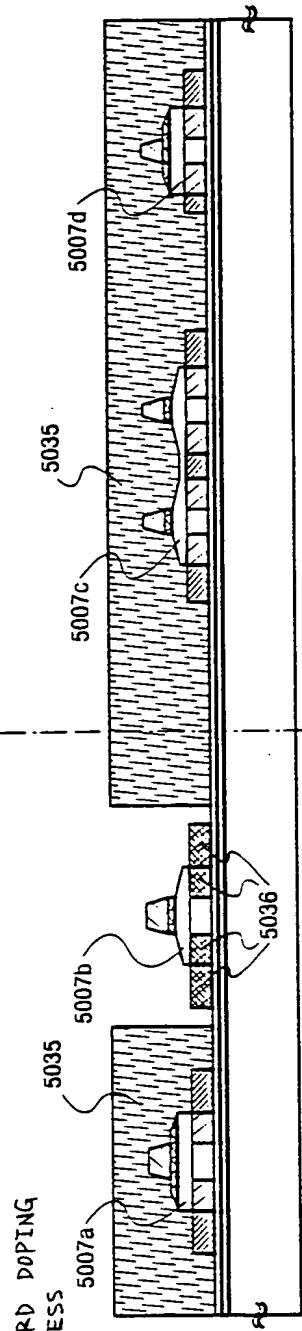


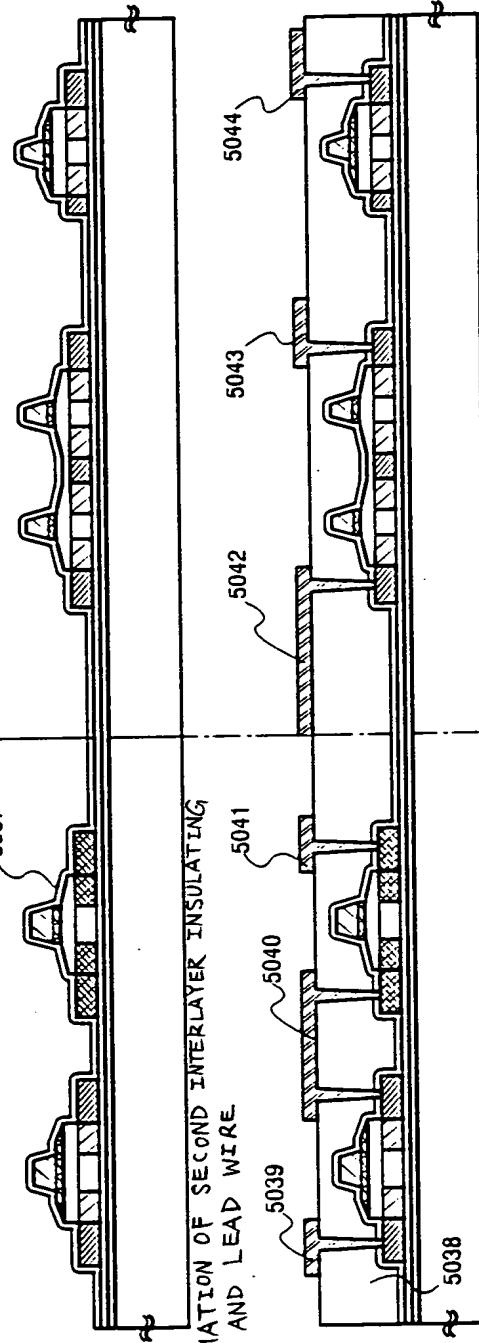
Fig.12(C) THIRD DOPING PROCESS



பொது தொழில்நுட்பம்

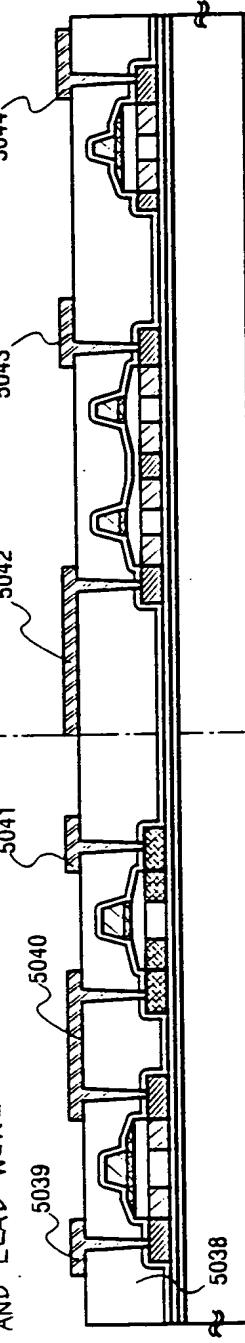
FORMATION OF FIRST INTER-LAYER
INSULATING FILM / ACTIVATION PROCESS

Fig.13(A)



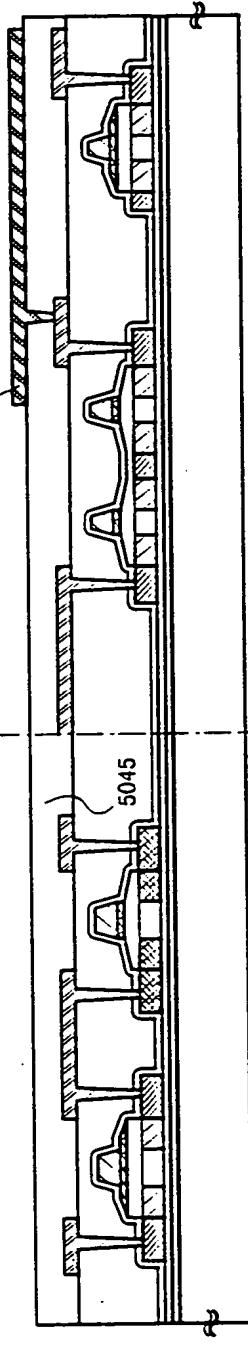
FORMATION OF SECOND INTER-LAYER INSULATING
FILM AND LEAD WIRE

Fig.13(B)



FORMATION OF THIRD INTER-LAYER INSULATING FILM
AND REFLECTION ELECTRODE

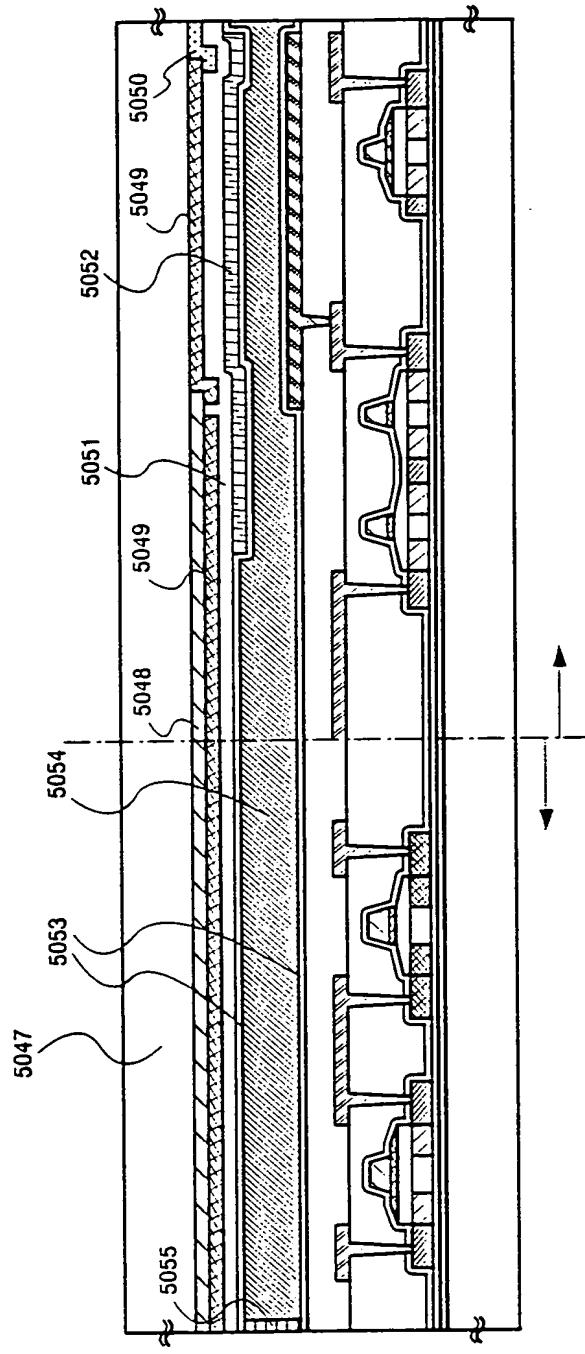
Fig.13(C)



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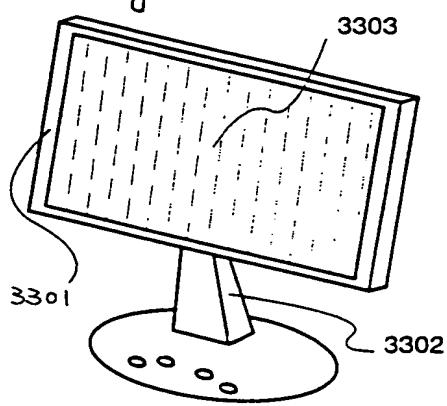
FORMATION OF OPPOSING SUBSTRATE / INJECTION OF LIQUID CRYSTAL MATERIAL

Fig.14



TOKUYO-2004-660

Fig.15(A)



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Fig.15(B)

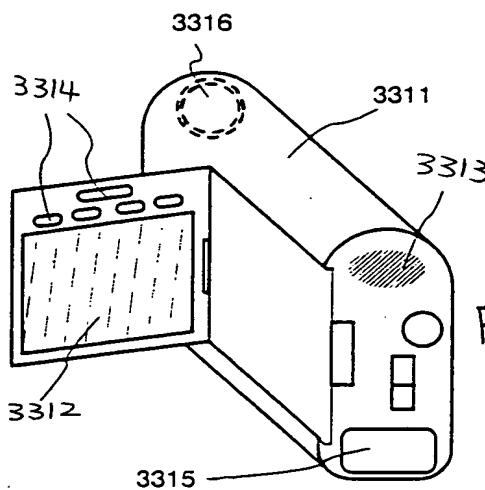
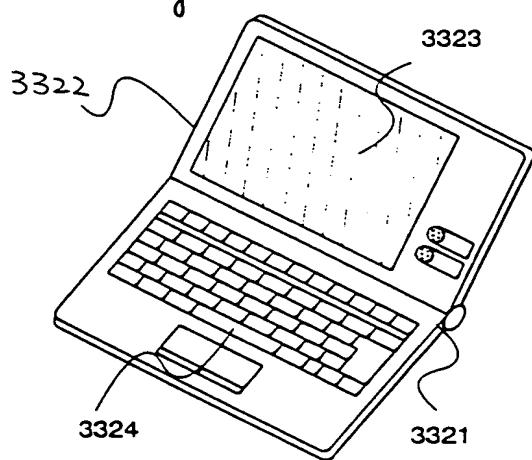


Fig.15(C)



3335

PC CARD

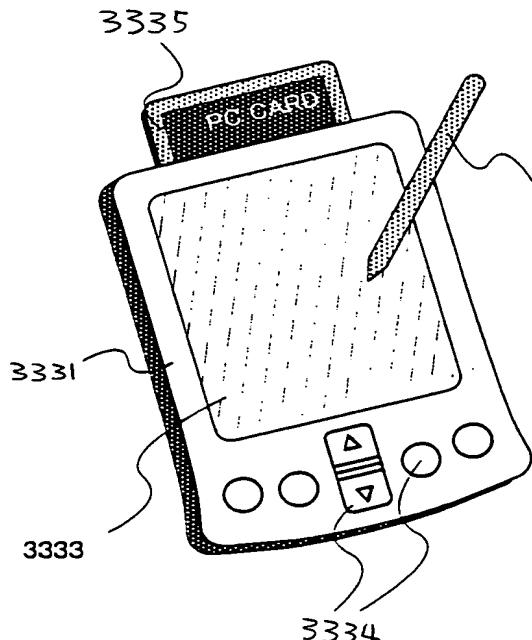
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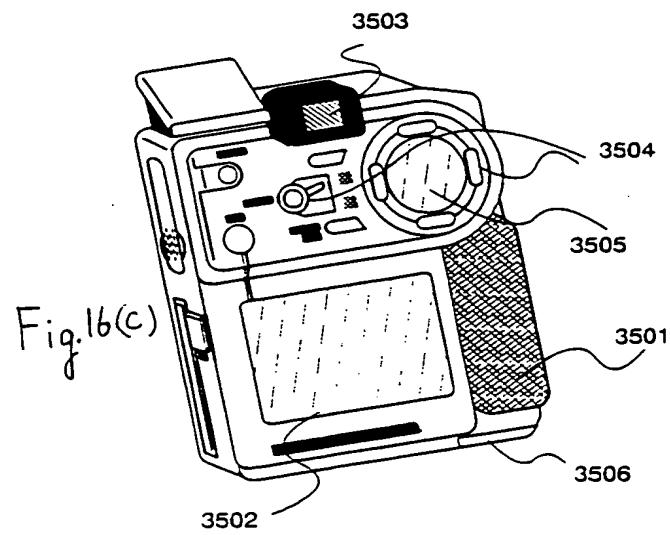
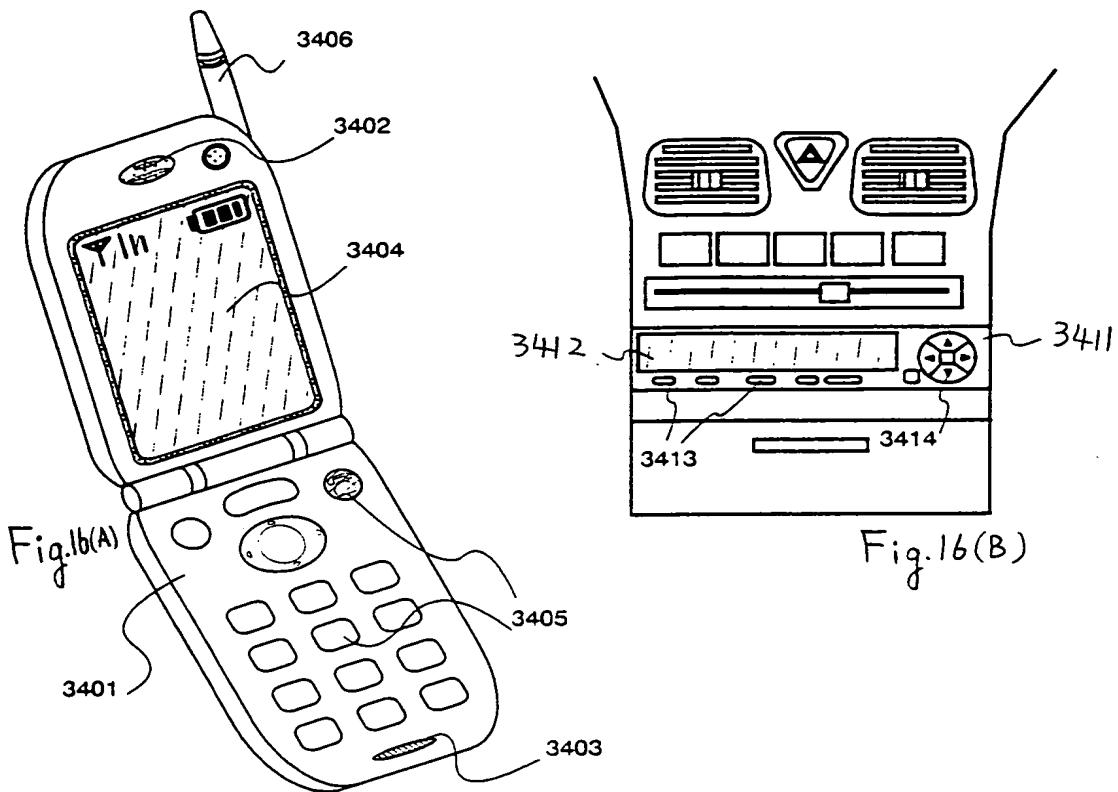
3333

3334

Fig.15(D)



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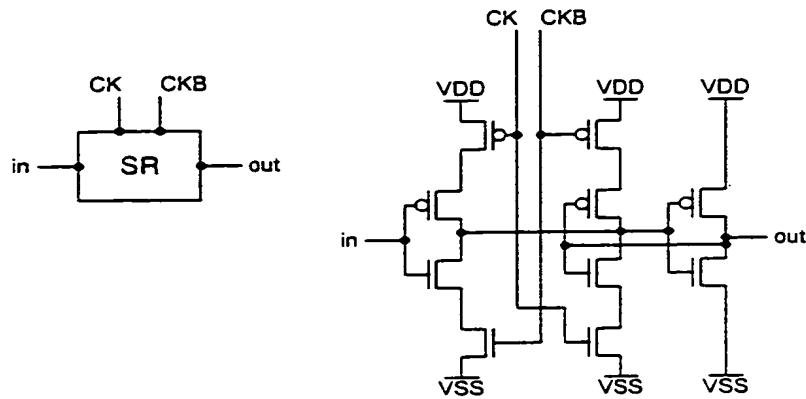


Fig. 17(A)

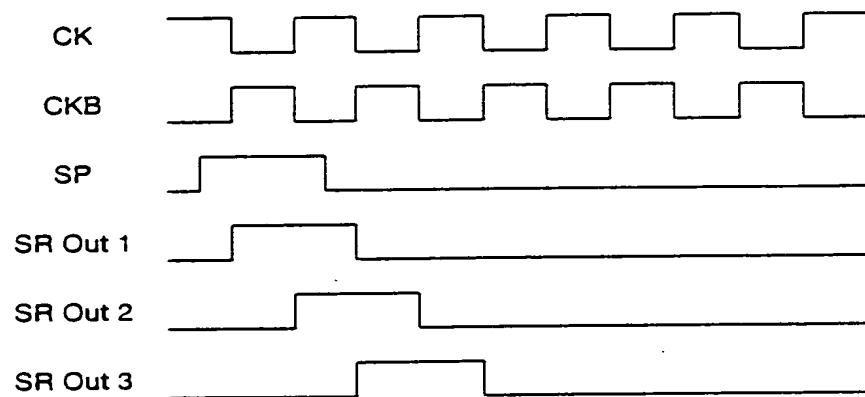


Fig. 17(B)